

# Pradip Dalapati

## List of Publications by Year in descending order

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Version: 2024-02-01

28  
papers

230  
citations

840776

11  
h-index

1058476

14  
g-index

28  
all docs

28  
docs citations

28  
times ranked

132  
citing authors

#	ARTICLE	IF	CITATIONS
1	Polarization-resolved photoluminescence study of an atom probe tip containing a ZnO-(Mg,Zn)O heterostructure. , 2022, , .		1
2	The role of p-GaN layer thickness for the evaluation of high-performance and ultrafast GaInN/GaN multiple quantum wells UV photodetectors. Optical Materials, 2022, 127, 112284.	3.6	5
3	Impact of current-induced degradation process on the electro-optical characteristics of InGaN/GaN multiple-quantum-well photodetectors fabricated on sapphire substrate. Applied Physics Letters, 2021, 118, .	3.3	12
4	<i>In Situ</i> Spectroscopic Study of the Optomechanical Properties of Evaporating Field Ion Emitters. Physical Review Applied, 2021, 15, .	3.8	6
5	Understanding the degradation mechanisms of InGaN/GaN multiple quantum well UV photodetectors submitted to different current stresses. Optics Letters, 2021, 46, 3568.	3.3	5
6	Improved epilayer qualities and electrical characteristics for GaInN multiple-quantum-well photovoltaic cells and their operation under artificial sunlight and monochromatic light illuminations. AIP Advances, 2021, 11, .	1.3	4
7	Bias-controlled photocurrent generation process in GaN-based ultraviolet p&eacute;i&eacute;n photodetectors fabricated with a thick Al <sub>2</sub> O <sub>3</sub> passivation layer. Optik, 2021, 245, 167691.	2.9	12
8	Evaluation of high-performance, self-powered and wavelength-selective InGaN/GaN multiple quantum well UV photodetectors fabricated on sapphire substrate: Analysis of the influence of growth temperature. Sensors and Actuators A: Physical, 2021, 331, 113050.	4.1	11
9	Current-induced degradation process in (In)AlGaIn-based deep-UV light-emitting diode fabricated on AlN/sapphire template. Optical Materials, 2020, 109, 110352.	3.6	19
10	InGaIn Quantum Dots Studied by Correlative Microscopy Techniques for Enhanced Light-Emitting Diodes. ACS Applied Nano Materials, 2020, 3, 10133-10143.	5.0	5
11	Investigation of AlGaIn/GaN high electron mobility transistors on Silicon (111) substrates employing multi-stacked strained layer superlattice structures. Superlattices and Microstructures, 2020, 147, 106709.	3.1	13
12	Analysis of the Temperature Dependence of Diode Ideality Factor in InGaIn-Based UV-A Light-Emitting Diode. Semiconductors, 2020, 54, 1284-1289.	0.5	3
13	A photonic atom probe coupling 3D atomic scale analysis with in situ photoluminescence spectroscopy. Review of Scientific Instruments, 2020, 91, 083704.	1.3	16
14	Super-resolution Optical Spectroscopy of Nanoscale Emitters within a Photonic Atom Probe. Nano Letters, 2020, 20, 8733-8738.	9.1	8
15	Temperature dependence of current&eacute;voltage and carrier lifetime characteristics in InGaIn blue light-emitting diode. Optical and Quantum Electronics, 2020, 52, 1.	3.3	6
16	Temperature induced carrier transition and its effect on optical intensity of InGaIn-based light-emitting diodes. Optik, 2020, 212, 164722.	2.9	2
17	Reliability of Ultraviolet Light-Emitting Diodes. Solid State Lighting Technology and Application Series, 2019, , 397-424.	0.3	2
18	Effect of Temperature on Electro-Optical Characteristics of Silicon Based p-n Photodiode (VTB8440BH). Silicon, 2018, 10, 2547-2553.	3.3	2

#	ARTICLE	IF	CITATIONS
19	Effect of temperature on intensity and forward tunneling current in GaP-based green light emitting diode. <i>Journal of Optics (India)</i> , 2017, 46, 68-74.	1.7	1
20	Influence of temperature on different optoelectronic characteristics of InGaN light emitting diodes. <i>Optical and Quantum Electronics</i> , 2017, 49, 1.	3.3	5
21	Studies on the Effect of Temperature on Electroluminescence, Current-Voltage, and Carrier Lifetimes Characteristics in a InGaN/Sapphire Purple Light Emitting Diode. <i>Journal of Electronic Materials</i> , 2016, 45, 2683-2691.	2.2	8
22	Effect of temperature on the opto-electrical properties of GaP based light emitting diodes. <i>Optik</i> , 2016, 127, 2598-2602.	2.9	5
23	Effect of temperature on light-current ( $I_L$ ) characteristics of GaAlAs based infrared emitter. <i>Optik</i> , 2015, 126, 2242-2246.	2.9	5
24	Influence of temperature on the performance of high power AlGaInP based red light emitting diode. <i>Optical and Quantum Electronics</i> , 2015, 47, 1227-1238.	3.3	18
25	Study of effective carrier lifetime and ideality factor of BPW 21 and BPW 34B photodiodes from above room temperature to liquid nitrogen temperature. <i>Cryogenics</i> , 2015, 65, 10-15.	1.7	13
26	Influence of temperature on tunneling-enhanced recombination in Si based p-n photodiodes. <i>Journal of Semiconductors</i> , 2014, 35, 082001.	3.7	12
27	Tunneling current in Si-doped n type-GaAs heterostructures infrared emitter. <i>Frontiers of Optoelectronics</i> , 2014, 7, 501-508.	3.7	12
28	Effect of temperature on the intensity and carrier lifetime of an AlGaAs based red light emitting diode. <i>Journal of Semiconductors</i> , 2013, 34, 092001.	3.7	19